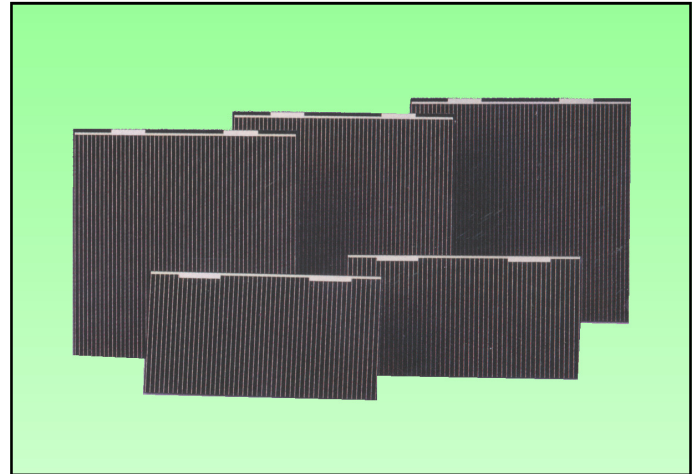


## GalnP<sub>2</sub>/GaAs/Ge Dual Junction Solar Cells

### Features

- High efficiency n/p design
  - Integral bypass diode protection
  - Transparent insertion into existing systems
- High volume production capability:
  - Currently delivering 21.5% minimum average efficiency solar cells



### Product Description

Substrate	Germanium
Method of GaAs Growth	Metal Organic Vapor Phase Epitaxy
Device Design	Monolithic, two terminal dual junction. n/p GalnP <sub>2</sub> and GaAs solar cells interconnected with a tunnel junction
Sizes	Up To 30 cm <sup>2</sup>
Assembly Method	Multiple techniques including soldering, welding, thermocompression, or ultrasonic wire bonding
Integral Diode	Si diode integrated into recess on back side

Note: Other Variations Are Available Upon Request

### Heritage

- More than 2000 kW of multi-junction cells produced
- More than 675 kW of multi-junction arrays *on orbit*
- 1 MW annual capacity - cells, panels & arrays
- On orbit performance for multi-junction solar cells validated to  $\pm 1.5\%$  of ground test results

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### Typical Electrical Parameters

(AMO (135.3 mW/cm<sup>2</sup>) 28 °C, Bare Cell)

J<sub>sc</sub>= 15.05 mA/cm<sup>2</sup>

J<sub>mp</sub>= 14.15 mA/cm<sup>2</sup>

J<sub>load min avg</sub>= 14.20 mA/cm<sup>2</sup>

V<sub>oc</sub>= 2.360 V

V<sub>mp</sub>= 2.085 V

V<sub>load</sub>= 2.050 V

C<sub>ff</sub>= 0.83

Eff<sub>load</sub>= 21.5%

Eff<sub>mp</sub>= 21.8%

### Radiation Degradation

(Fluence 1MeV Electrons/cm<sup>2</sup>)

Parameters	1x10 <sup>14</sup>	5x10 <sup>14</sup>	1x10 <sup>15</sup>
I <sub>mp</sub> /I <sub>mp0</sub>	1.00	0.96	0.92
V <sub>mp</sub> /V <sub>mp0</sub>	0.96	0.93	0.91
P <sub>mp</sub> /P <sub>mp0</sub>	0.96	0.89	0.83

### Thermal Properties

Solar Absorptance= 0.92 (Ceria Doped Microsheet)

Emittance (Normal)= 0.85 (Ceria Doped Microsheet)

### Weight

84 mg/ cm<sup>2</sup> (Bare) @ 140 μm (5.5 mil) Thickness

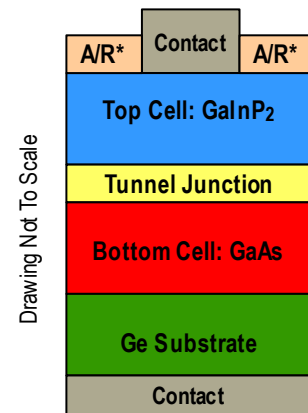
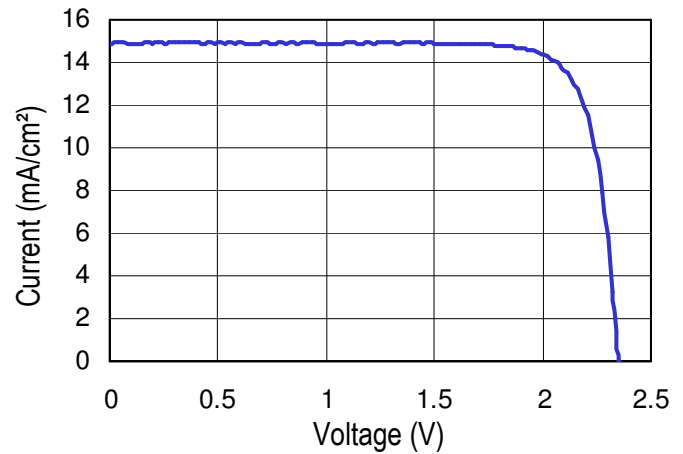
Thickness of 175 μm typical with weight equivalence of a 140 μm thick cell.

### Temperature Coefficients

Parameters	BOL	1x10 <sup>15</sup> (1 MeV e/cm <sup>2</sup> )
J <sub>mp</sub> (μA/cm <sup>2</sup> /°C)	8	13
J <sub>sc</sub> (μA/cm <sup>2</sup> /°C)	10	12
V <sub>mp</sub> (mV/°C)	-4.6	-5.0
V <sub>oc</sub> (mV/°C)	-4.2	-4.8

### Typical IV Characteristic

AMO (135.3 mW/cm<sup>2</sup>) 28 °C, Bare Cell



\*A/R: Anti-Reflective Coating

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The information contained on this sheet is for reference only. Specifications subject to change without notice. 4/29/2008